Discrete POWER & Signal **Technologies** 

# **MPS6562**

**MPS6562** 

FAIRCHILD

SEMICONDUCTOR TM



# **PNP General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA. Sourced from Process 67. See TN4033A for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	25	V
V <sub>CBO</sub>	Collector-Base Voltage	25	V
$V_{\text{EBO}}$	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	1.0	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Max	Units	
		MPS6562		
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W	
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W	

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# PNP General Purpose Amplifier (continued)

Electri	Electrical Characteristics TA = 25°C unless otherwise noted				
Symbol	Parameter	Test Conditions	Min	Мах	Units

# OFF CHARACTERISTICS

V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	25		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, I_{\rm E} = 0$	25		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E} = 100 \ \mu A, I_{C} = 0$	5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 20 \text{ V}, \text{ I}_{E} = 0$		100	nA
I <sub>CEO</sub>	Collector Cutoff Current	$V_{CE} = 25 \text{ V}, \text{ I}_{E} = 0$		100	nA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		100	nA

### **ON CHARACTERISTICS\***

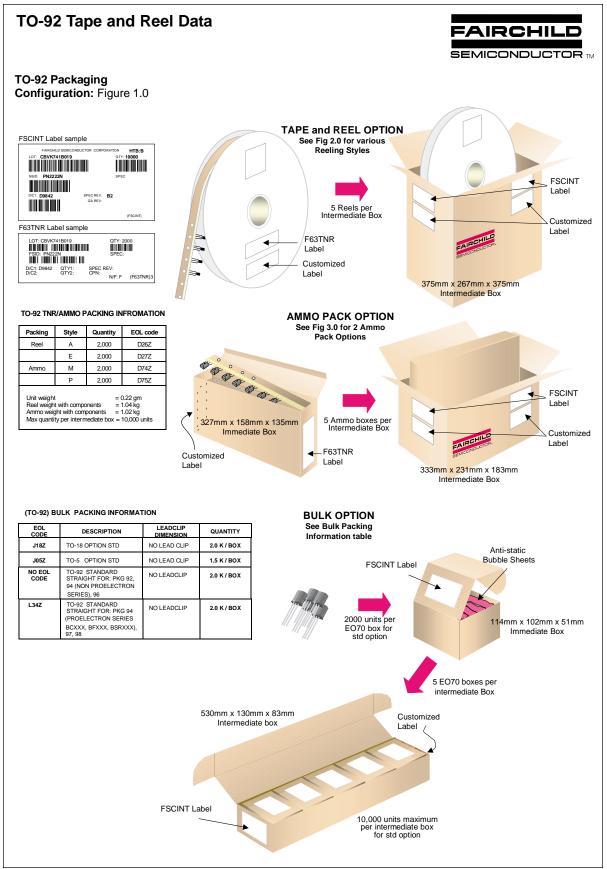
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	35		
		$V_{CE} = 1.0 \text{ V}, I_{C} = 100 \text{ mA}$	50		
		$V_{CE} = 1.0 \text{ V}, I_{C} = 500 \text{ mA}$	50	200	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 50 \text{ mA}$		0.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$V_{CE} = 1.0 \text{ V}, I_C = 500 \text{ mA}$		1.2	V

## SMALL SIGNAL CHARACTERISTICS

C <sub>ob</sub>	Output Capacitance	$V_{CB} = 10 \text{ V}, \text{ f} = 100 \text{ kHz}$		30	pF
f <sub>T</sub>	Current Gain - Bandwidth product	$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 20 MHz	60		MHz

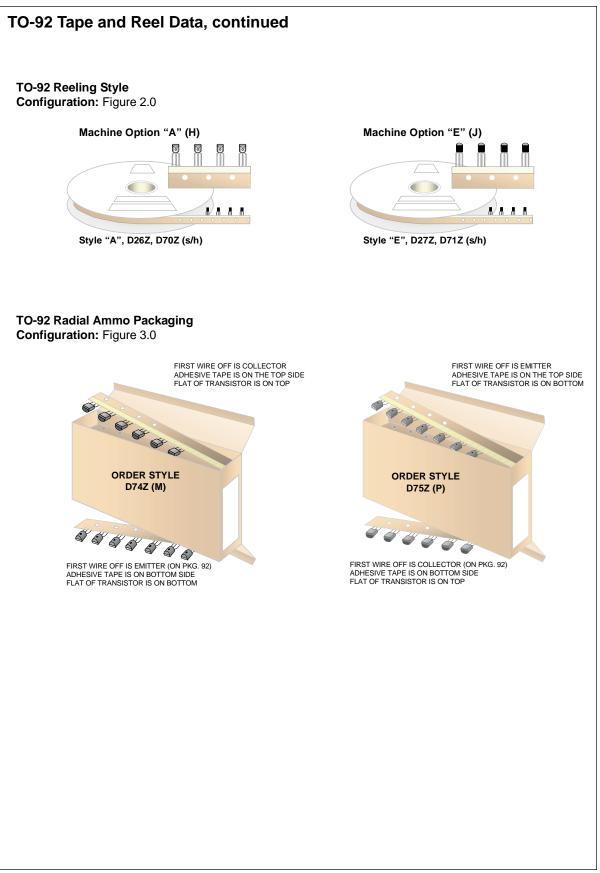
\*Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

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**Definition of Terms** 

Datasheet Identification	Product Status	Definition
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